	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	Er
1	BRS	L1	8	"6294420"	94.00.00.00.00.00.00.00.00.00.00.00.00.00	2003/08/2 6 13:23			0
2	BRS	L2	6	" 6358810"	USP AT; US-P GPU B; O; JPO; DER WEN T;	2003/08/2 6 13:23			0
3	BRS	L3	3	"6372530"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 13:24	,		0
4	BRS	L4	17	1 or 2 or 3	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 13:24			0
5	BRS	L5	5	4 and ((aluminum adj1 nitride) or AIN)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 13:26			0
6	BRS	L6	5	5 and ((capacitor adj1 dielectric) or dielectric)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:06			0
7	BRS	L7	5	6 and ((aluminum adj1 nitride) or AIN or aluminum or nitride or nitrogen)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 13:38			0
8	BRS	L8	10	"6218293"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 13:38			О
9	BRS	L10	1	9 and DRAM	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 13:39	ī.		0
10	BRS	L9	10	8 and ((aluminum adj1 nitinde) or AIN or aluminum or nitinde or nitrogen)	USP AT; US-P GPU B; EPO; JPO; DER WEA T;	2003/08/2 6 14:07			0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	LO EL
11	BRS	L11	8	9 and capacitor	USP AT; P USP; O; O; BEPOREN T; DEST;	2003/08/2 6 14:17			0
12	BRS	L12	7	11 and (memory or cell or storage or FET or transistor or source or drain)	USP AT; US-P GPU B;	2003/08/2 6 14:57			0
13	BRS	L13	1	12 and (DRAM or (dynamic adj1 rom adj1 access adj1 memory))	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:08			О
14	BRS	L14	6	12 and (bitlines or bit or lines or word or wordlines or array)	JPO; JPO; DER WEN T;	2003/08/2 6 13:50			О
15	BRS	L15	7671 6	(DRAM or (dynamic adj1 rom adj1 access adj1 memory))	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:05			0
16	BRS	L16	23	"5536193"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:06			0
17	BRS	L17	15	16 and ((capacitor adj1 dielectric) or dielectric)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:18			0
18	BRS	L19	0	18 and (DRAM or (dynamic adj1 rom adj1 access adj1 memory))	JPO; DER WEN T;	2003/08/2 6 14:24			0
19	BRS	L18	14	17 and ((aluminum adj1 nitride) or AIN or aluminum or nitride or nitrogen)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:45			0
20	BRS	L20	6	"6307775"	USP AT; US-F GPU B; EPO JPO; DER WEN T;	2003/08/2 6 14:13			0

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_	Туре	L#	Hits	Search Text	DBs USP	Stamp	nts	Error Definition	10
21	BRS	L21	6	"5573742"	AT; US-P GPU B;	2003/08/2 6 14:17			О
22	BRS	L22	2544 6	15 and capacitor	USP AT; US-P GPU B;	2003/08/2 6 14:18			О
23	BRS	L23	2049 8	22 and ((capacitor adj1 dielectric) or dielectric or storage or array or memory or cell)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:23			0
24	BRS	L24	2037 3	23 and (memory or cell or storage or FET or transistor or source or drain or billines or bit or line or word or wordlines)	B; EPO;	2003/08/2 6 14:20			0
25	BRS	L27	14	"6015990"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:23			0
26	BRS	L28	12	27 and ((capacitor adj1 dielectric) or dielectric or storage or array or memory or cell)	USP AT; US-P GPU B:	2003/08/2 6 14:56			0
27	BRS	L29	8	28 and ((aluminum adj1 nitride) or AIN or aluminum or nitride or nitrogen)	USP AT; US-P GPU B;	2003/08/2 6 14:56			0
28	BRS	L30	4	29 and (DRAM or (dynamic adj1 rom adj1 access adj1 memory))	USP AT; US-P GPU B;	2003/08/2 6 14:57			o
29	BRS	L31	65	"4460670"	USP AT; US-P GPU B;	2003/08/2 6 14:52			0
30	BRS	L32	33	"4507673"	USP AT; US-P GPU B;	2003/08/2 6 14:52			0

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	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	Er
31	BRS	L33	15	"465769 9 "	USP AT; USPU B; O; DER VEN T;	2003/08/2 6 14:52			О
32	BRS	L34	18	"4462150"	USP AT; -P GPU B; PO; DER VEN T;	2003/08/2 6 14:52			0
33	BRS	L35	10	"4738729"	JPO; DER WEN T;	2003/08/2 6 14:52			o
34	BRS	L36	6	"4768072"	JPO; DER WEN T;	2003/08/2 6 14:52			О
35	BRS	L37	46	"4769686"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:53			0
36	BRS	L38	23	"4656101"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:53			0
37	BRS	L39	9	"5356608"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:53			0
38	BRS	L40	26	"5605858"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:53			0
39	BRS	L41	47	" 5687112"	JPO; DER WEN T;	2003/08/2 6 14:53			0
40	BRS	L42	18	"5767578"	USP AT; US-P GPU B; JPO; JPO; DER WEN T;	2003/08/2 6 14:53			0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	Er
41	BRS	L43	19	"5773882"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:54			0
42	BRS	L44	18	" 5783483 "	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:54			0
43	BRS	L45	18	"5783716"	USP AT; US-P GPU B; JPO; JPO; DER WEN T;	2003/08/2 6 14:54			0
44	BRS	L46	30	"5786259"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:54			0
45	BRS	L47	23	"5786635"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:54			0
46	BRS	L48	5777 5	31 or 32 ore 33 or 34 or35 or 36 or 37 or 38 or 39 or 40 or 41 or 42 or 43 or 44 or 45 or 46 or 47	USP AT; US-P GPU B;	2003/08/2 6 14:55			0
47	BRS	L49	353	31 or 32 or 33 or 34 or 35 or 36 or 37 or 38 or 39 or 40 or 41 or 42 or 43 or 44 or 45 or 46 or 47		2003/08/2 6 14:55			0
48	BRS	L50	290	49 and ((aluminum adj1 nitrde) or AlN or aluminum or nitride or nitrogen)	USP AT; US-P GPU B;	2003/08/2 6 14:59			0
49	BRS	L51	226	50 and ((capacitor adj1 dlelectric) or diefectric or storage or array or memory or cell)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:46			0
50	BRS	L52	198	51 and (memory or cell or storage or FET or transistor or source or drain)	USP AT; US-P GPU B;	2003/08/2 6 15:54			0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	Er ro
51	BRS	L53	77	52 and (DRAM or (dynamic adj1 rom adj1 access adj1 memory))	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 14:58			0
52	BRS	L54	30	53 and ((aluminum adj1 nitride) or AlN)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:45			0
53	BRS	L55	6	"6204595"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:45			0
54	BRS	L56	1	55 and ((aluminum adj1 niiride) or AIN)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:48			0
55	BRS	L57	1	56 and ((capacitor adj1 dielectric) or dielectric or storage or amay or memory or cell)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:50			0
56	BRS	L58	4	"6514113"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:47			0
57	BRS	L59	0	58 and ((aluminum adj1 nitride) or AIN)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:48			0
58	BRS	L60	0	"6268686"	P. P. O;;R Z ST: SP. O;;R Z SB: SPEE SEE SEE SEE SEE SEE SEE SEE SEE SEE	2003/08/2 6 15:48			0
59	BRS	L61	4	"6268686"	USP AT; US-P GPU B;	2003/08/2 6 15:48			0
60	BRS	L62	0	61 and ((aluminum adj1 nitride) or AIN)	USP AT; US-P GPU B;	2003/08/2 6 15:49			0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	E
61	BRS	L63	14	"5763997"	USP AT; USPU B; O; EPO; DER VEN T;	2003/08/2 6 15:49			0
62	BRS	L64	o	63 and ((aluminum adj1 nitride) or AIN)	USP AT; US-P GPU B;	2003/08/2 6 15:49			0
63	BRS	L65	8	"6181056"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:49			0
64	BRS	L66	0	65 and ((aluminum adj1 nitride) or AIN)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:53		,	0
65	BRS	L67	5	"6218771"	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:50			0
66	BRS	L68	3224 7	67and ((aluminum adj1 nitride) or AIN)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:50			0
67	BRS	L69	1	67 and ((aluminum adj1 nitride) or AIN)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:50			0
68	BRS	L70	1	69 and ((capacitor adj1 dielectric) or dielectric or storage or array or memory or cell)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:53			0
69	BRS	L71	7011	("257/68") or ("257/301") or ("257/295") or ("257/311") or ("257/296") or ("257/71")	USP AT; US-P GPU B;	2003/08/2 6 15:53			0
70	BRS	L72	157	71 and ((aluminum adj1 nitride) or AIN)	USP AT; US-P GPU B;	2003/08/2 6 15:53			0

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	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	Εr
71	BRS	L73	153	72 and ((capacitor adj1 dielectric) or dielectric or storage or array or memory or cell)	USP AT; US-P GPU B; EPO; JPO; DER WEN T;	2003/08/2 6 15:53	•		0
72	BRS	L74	144	73 and (memory or cell or storage or FET or transistor or source or drain)	B;	2003/08/2 6 15:54			0